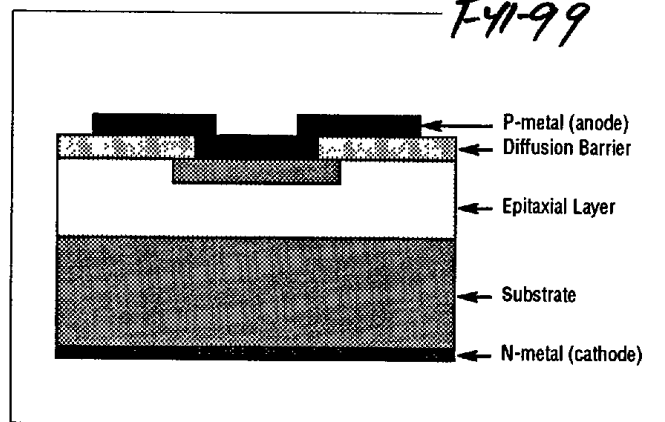
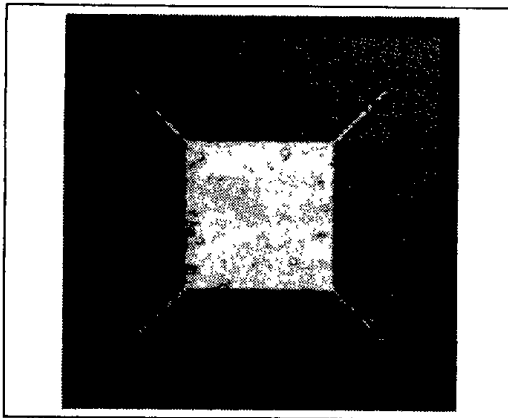


**SIEMENS****RP-12C**  
**Mask-Diffused GaAsP LED****PART NO. 2680-7075**Custom  
Optoelectronic  
Products**DESCRIPTION**

Siemens RP-12C is a mask-diffused GaAsP light-emitting diode. With a bright and uniform 655 nm emission, this device is ideal for lamp and display applications.

**MATERIAL**

Epitaxial Layer:  $\text{GaAs}_{1-x}\text{P}_x : \text{Te}$   
 Substrate: GaAs : Si or GaAs : Te  
 Metalizations: Anode Aluminum  
                   Cathode Gold-Germanium

Dimensions  
 (center to center): Height 0.012"  
                           Width 0.012"  
                           Thickness 0.010"

**TYPICAL DEVICE PARAMETERS**

|                             |           |                    |                     |
|-----------------------------|-----------|--------------------|---------------------|
| Forward I-V Characteristics | $V_{F3}$  | 1.70 V             | @ 20 mA             |
|                             | $V_{F2}$  | 1.64 V             | @ 10 mA             |
|                             | $V_{F1}$  | 1.45 V             | @ 100 $\mu\text{A}$ |
| Reverse I-V Characteristics | $V_{R1}$  | -25.0 V            | @ -10 $\mu\text{A}$ |
| Peak EL Wavelength          | $\lambda$ | 655 nm             | @ 20 mA             |
| Spectral Half-Width         | FWHM      | 40 nm              | @ 20 mA             |
| Luminous Intensity          | LI        | 500 $\mu\text{Cd}$ | @ 10 mA             |